

In the Claims:

Please rewrite Claims 1, 8, and 11 as follows.

a 1. (ONCE AMENDED) A method of planarizing substrates having shallow trench isolation, comprising:

providing a substrate;

forming trenches in said substrate;

depositing a layer of dielectric on said substrate  
thereby filling said trenches with said dielectric;

forming a layer of resist on said layer of dielectric;

providing a polishing pad having a hardness of at least Shore "D" 52; and

removing all of said layer of resist and part of said layer of dielectric using said polishing pad and chemical mechanical polishing thereby leaving said trenches filled with trench dielectric and forming a planar surface.

a<sup>2</sup> 8. (ONCE AMENDED) The method of claim 1 wherein said removing said layer of resist and part of said layer of dielectric removes that part of said layer of dielectric above said substrate.

11. (ONCE AMENDED) A method of planarizing substrates having shallow trench isolation, comprising:

- providing a substrate;
- forming a dielectric base on said substrate;
- forming trench openings in said dielectric base;
- forming trenches in said substrate directly below said trench openings in said dielectric base;
- depositing a layer of trench dielectric on said dielectric base thereby filling said trenches with said trench dielectric;
- forming a layer of resist on said layer of trench dielectric;
- providing a polishing pad having a hardness of at least Shore "D" 52; and
- removing all of said layer of resist and part of said layer of trench dielectric using said polishing pad and chemical mechanical polishing thereby leaving trench dielectric in said trenches and forming a planar surface.